

Jagritee Talukdar

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	A Reliability Study of Non-uniform Si TFET with Dual Material Source: Impact of Interface Trap Charges and Temperature. Silicon, 2022, 14, 4515-4521.	3.3	1
2	Flicker Noise Analysis of Non-uniform Body TFET with Dual Material Source (NUTFET-DMS). Lecture Notes in Electrical Engineering, 2022, , 247-253.	0.4	0
3	Analytical modeling and TCAD simulation for subthreshold characteristics of asymmetric Tunnel FET. Materials Science in Semiconductor Processing, 2022, 142, 106482.	4.0	4
4	Source pocket-engineered hetero-gate dielectric SOI Tunnel FET with improved performance. Materials Science in Semiconductor Processing, 2022, 143, 106541.	4.0	7
5	Noise behavior and reliability analysis of non-uniform body tunnel FET with dual material source. Microelectronics Reliability, 2022, 131, 114510.	1.7	3
6	Low Frequency Noise Analysis of Single Gate Extended Source Tunnel FET. Silicon, 2021, 13, 3971-3980.	3.3	16
7	Impact of temperature and different types of trap charges on noise behavior of Non-uniform Body with Dual Material Source TFET (NUTFET-DMS). , 2021, , .		0
8	Impact of temperature counting the effect of back gate bias on the performance of extended source tunnel FET (ESTFET) with $\hat{I}p+$ SiGe pocket layer. Applied Physics A: Materials Science and Processing, 2021, 127, 1.	2.3	6
9	Dielectrically Modulated Single and Double Gate Tunnel FET Based Biosensors for Enhanced Sensitivity. IEEE Sensors Journal, 2021, 21, 26566-26573.	4.7	21
10	A non-uniform silicon TFET design with dual-material source and compressed drain. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	27
11	A Novel Extended Source TFET with $\hat{I}p+$ SiGe Layer. Silicon, 2020, 12, 2273-2281.	3.3	45
12	Device physics based analytical modeling for electrical characteristics of single gate extended source tunnel FET (SG-ESTFET). Superlattices and Microstructures, 2020, 148, 106725.	3.1	11
13	Comparative Analysis of the Effects of Trap Charges on Single- and Double-Gate Extended-Source Tunnel FET with $\hat{I}p+$ SiGe Pocket Layer. Journal of Electronic Materials, 2020, 49, 4333-4342.	2.2	22